

AMENDMENTS TO THE CLAIMS:

1. (Original) An atomic layer deposition method comprising:

respectively loading a plurality of substrates into a plurality of reaction cells, the plurality of reaction cells being disposed in a reaction chamber; and

alternately and repeatedly applying various vapor substances onto each substrate such that a thin film is formed on each substrate, wherein a plurality of vapor injection pipes each injecting one of the vapor substances periodically scans over each substrate to apply the various vapor substances alternatively and repeatedly onto each substrate.
2. (Original) The method of claim 1, wherein each substrate is heated using a heater disposed in the reaction chamber.
3. (Original) The method of claim 1, wherein RF power is applied to the vapor injection pipes such that plasma is generated in the reaction chamber.
- 4-14 (Cancelled)
15. (New) The method of claim 1, wherein alternately and repeatedly applying vapor substances comprises:

relatively rotating each vapor injection pipe with respect to the plurality of substrates; and

periodically applying one of the vapor substances onto each substrate.

16. (New) The method of claim 15, further comprising controlling a relative rotation speed of each vapor injection pipe with respect to the plurality of substrates.

17. (New) The method of claim 1, further comprising exhausting a remaining vapor substance out of the reaction chamber through a plurality of exhausting portion.

18. (New) The method of claim 17, wherein the each exhausting portion is disposed on a surface of the chamber on which a corresponding susceptor resides, near the corresponding susceptor.

19. (New) The method of claim 1, further comprising applying an RF power to the plurality of vapor injection pipes.

20. (New) The method of claim 1, wherein each vapor substance applied onto the substrate reacts with the same substrate only by a partition wall separating each substrate from the others.